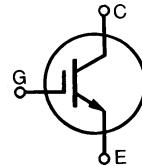


Ultra-Low $V_{CE(sat)}$ IGBT

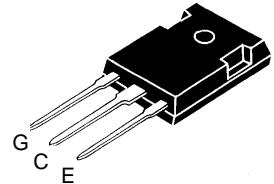
IXGH 41N60

V_{CES} = 600 V
 I_{C25} = 76 A
 $V_{CE(sat)}$ = 1.6 V



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C	600	V
V_{CGR}	T_J = 25°C to 150°C; $R_{GE} = 1 \text{ M}\Omega$	600	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_c = 25°C	76	A
I_{C90}	T_c = 90°C	41	A
I_{CM}	T_c = 25°C, 1 ms	152	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 10 \Omega$ Clamped inductive load, $L = 100 \mu\text{H}$	$I_{CM} = 76$ @ 0.8 V_{CES}	A
P_c	T_c = 25°C	200	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
M_d	Mounting torque (M3)	1.13/10	Nm/lb.in.
Weight		6	g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	°C

TO-247 AD



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- International standard package JEDEC TO-247 AD
- Newest generation HDMOS™ process
- Low $V_{CE(sat)}$
 - for minimum on-state conduction losses
- High current handling capability
- MOS Gate turn-on
 - drive simplicity

Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Solid state relays
- Lighting controls
- Temperature regulators

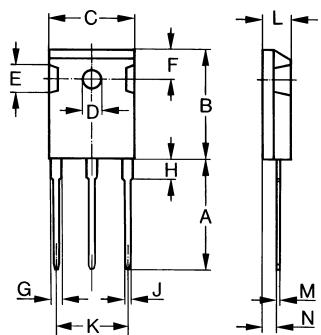
Advantages

- Easy to mount with 1 screw (isolated mounting screw hole)
- Low losses, high efficiency
- High power density

Symbol	Test Conditions	Characteristic Values		
		($T_J = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.
BV_{CES}	$I_C = 250 \mu\text{A}$, $V_{GE} = 0 \text{ V}$	600		V
$V_{GE(th)}$	$I_C = 250 \mu\text{A}$, $V_{CE} = V_{GE}$	2.5		5 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		200 μA 1 mA
I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$			±100 nA
$V_{CE(sat)}$	$I_C = I_{C90}$, $V_{GE} = 15 \text{ V}$			1.6 V

Symbol	Test Conditions	Characteristic Values			
		($T_J = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.	max.
g_{fs}	$I_C = I_{C90}$; $V_{CE} = 10 \text{ V}$, Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $\leq 2 \%$	19	28	S	
C_{ies}	$V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$	2750		pF	
C_{oes}		206		pF	
C_{res}		55		pF	
Q_g	$I_C = I_{C90}$, $V_{GE} = 15 \text{ V}$, $V_{CE} = 0.5 V_{CES}$	120		nC	
Q_{ge}		25		nC	
Q_{gc}		40		nC	
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C90}$, $V_{GE} = 15 \text{ V}$, $L = 100 \mu\text{H}$, $V_{CE} = 0.8 V_{CES}$, $R_G = R_{off} = 10 \Omega$ Remarks: Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$, higher T_J or increased R_G	30		ns	
t_{ri}		30		ns	
$t_{d(off)}$		600		ns	
t_{fi}		450		ns	
E_{off}		8		mJ	
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C90}$, $V_{GE} = 15 \text{ V}$, $L = 100 \mu\text{H}$, $V_{CE} = 0.8 V_{CES}$, $R_G = R_{off} = 10 \Omega$ Remarks: Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$, higher T_J or increased R_G	40		ns	
t_{ri}		40		ns	
E_{on}		0.3		mJ	
$t_{d(off)}$		800		ns	
t_{fi}		600		ns	
E_{off}		15		mJ	
R_{thJC}			0.62	K/W	
R_{thCK}		0.25		K/W	

TO-247 AD (IXGH) Outline



Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102